



DMP2123L

P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

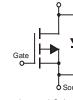
- Low R_{DS(ON)}:
 - $72 \text{ m}\Omega$ @V_{GS} = -4.5V
 - $108 \text{ m}\Omega$ @V_{GS} = -2.7V
 - 123 m Ω @V_{GS} = -2.5V
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 4)

Mechanical Data

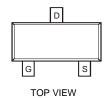
- Case: SOT-23
- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram Below
- Marking Information: See Page 4
- Ordering Information: See page 4
- Weight: 0.008 grams (approximate)



TOP VIEW



SOT-23



Internal Schematic

Maximum Ratings @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Value | Unit | |
|--|------------------|--------------|------|--|
| Drain-Source Voltage | V _{DSS} | -20 | V | |
| Gate-Source Voltage | V _{GSS} | ±12 | V | |
| · · · · · · · · · · · · · · · · · · · | 25°C 70°C | -3.0 -2.4 | A | |
| Pulsed Drain Current (Note 2) | I _{DM} | -15 | A | |
| Body-Diode Continuous Current (Note 1) | Is | 2.0 | Α | |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|--|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 1) | P_D | 1.4 | W |
| Thermal Resistance, Junction to Ambient (Note 1); Steady-State | $R_{	heta JA}$ | 90 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

Notes:

- 1. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t ≤10s.
- 2. Repetitive Rating, pulse width limited by junction temperature.
- 3. No purposefully added lead.
- 4. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

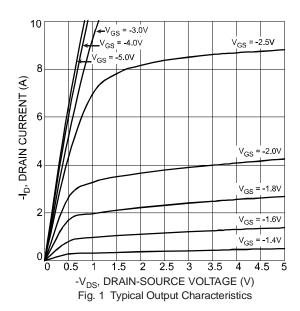


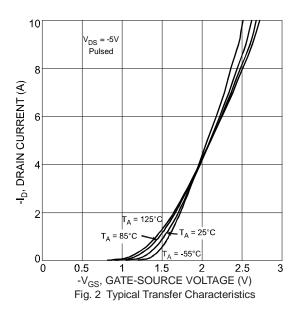
Electrical Characteristics @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|---|----------------------|------|------|-------|------|--|
| STATIC PARAMETERS | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | -20 | _ | _ | V | $I_D = -250 \mu A, V_{GS} = 0 V$ |
| Zero Gate Voltage Drain Current T _J = 25°C | I_{DSS} | _ | _ | -1 | μΑ | $V_{DS} = -20V, V_{GS} = 0V$ |
| Gate-Body Leakage Current | I _{GSS} | _ | _ | ±100 | nA | $V_{DS} = 0V, V_{GS} = \pm 12V$ |
| Gate Threshold Voltage | V _{GS(th)} | -0.6 | _ | -1.25 | V | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ |
| On State Drain Current (Note 5) | I _{D (ON)} | -15 | _ | _ | Α | $V_{GS} = -4.5V, V_{DS} = -5V$ |
| | | | 51 | 72 | | $V_{GS} = -4.5V$, $I_D = -3.5A$ |
| Static Drain-Source On-Resistance (Note 5) | R _{DS} (ON) | _ | 87 | 108 | mΩ | $V_{GS} = -2.7V, I_D = -3.0A$ |
| | | | 99 | 123 | | $V_{GS} = -2.5V, I_D = -2.6A$ |
| Forward Transconductance (Note 5) | g _{FS} | _ | 7.3 | _ | S | $V_{DS} = -10V, I_{D} = -3.0A$ |
| Diode Forward Voltage (Note 5) | V_{SD} | _ | 0.79 | -1.26 | V | $I_S = -1.7A$, $V_{GS} = 0V$ |
| Maximum Body-Diode Continuous Current (Note 1) | Is | _ | _ | 1.7 | Α | _ |
| DYNAMIC PARAMETERS (Note 6) | | | | | | |
| Total Gate Charge | Q_g | _ | 7.3 | _ | nC | $V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -3.0A$ |
| Gate-Source Charge | Q_{gs} | _ | 2.0 | _ | nC | $V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -3.0A$ |
| Gate-Drain Charge | Q_{gd} | _ | 1.9 | _ | nC | $V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_D = -3.0A$ |
| Turn-On Delay Time | t _{D(on)} | _ | 12 | _ | ns | |
| Turn-On Rise Time | | _ | 20 | _ | ns | $V_{DS} = -10V, V_{GS} = -4.5V,$ |
| Turn-Off Delay Time | | _ | 38 | _ | ns | $R_L = 10\Omega$, $R_G = 6\Omega$ |
| Turn-Off Fall Time | t _f | _ | 41 | _ | ns | |
| Input Capacitance | | _ | 443 | _ | рF | \\ 16\\\\\\ 0\\ |
| Output Capacitance | | _ | 128 | _ | рF | $V_{DS} = -16V, V_{GS} = 0V$ -f = 1.0MHz |
| Reverse Transfer Capacitance | C _{rss} | _ | 101 | _ | pF | 1 - 1.01/11/2 |

Notes:

- 5. Test pulse width $t = 300 \mu s$.
- 6. Guaranteed by design. Not subject to production testing.







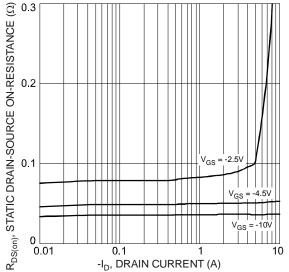


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

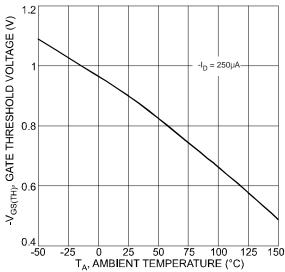


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

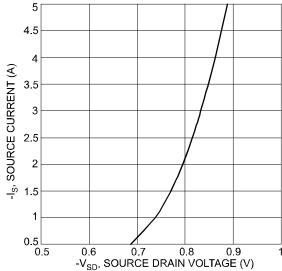
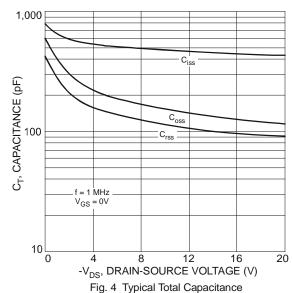


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage



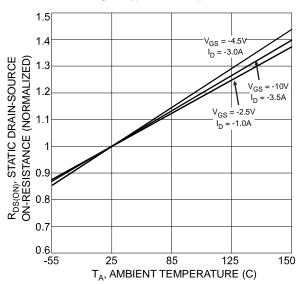


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

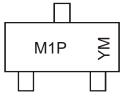


Ordering Information (Note 7)

| Part Number | Case | Packaging |
|-------------|--------|------------------|
| DMP2123L-7 | SOT-23 | 3000/Tape & Reel |

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



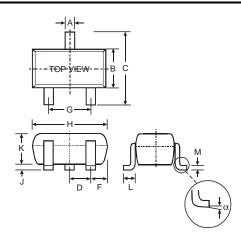
M1P = Product Type Marking Code YM = Date Code Marking

Y = Year ex: U = 2007 M = Month ex: 9 = September

Date Code Key

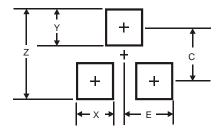
| Year | 20 | 07 | 20 | 08 | 20 | 09 | 20 | 10 | 20 | 11 | 20 | 12 |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code | l | J | \ | / | V | | , | Κ | ` | Y | 2 | 7 |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |

Package Outline Dimensions



| SOT-23 | | | | | |
|----------------------|-------------|-------|--|--|--|
| Dim | Min | Max | | | |
| Α | 0.37 | 0.51 | | | |
| В | 1.20 | 1.40 | | | |
| C | 2.30 | 2.50 | | | |
| D | 0.89 | 1.03 | | | |
| F | 0.45 | 0.60 | | | |
| G | 1.78 | 2.05 | | | |
| Η | 2.80 | 3.00 | | | |
| 7 | 0.013 | 0.10 | | | |
| K | 0.903 | 1.10 | | | |
| ٦ | L 0.45 0.61 | | | | |
| M | 0.085 | 0.180 | | | |
| α | 0° | 8° | | | |
| All Dimensions in mm | | | | | |
| | | | | | |

Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 2.9 |
| Х | 0.8 |
| Υ | 0.9 |
| С | 2.0 |
| E | 1.35 |

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